

FEATURE

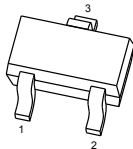
- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

APPLICATION

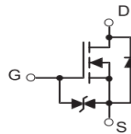
- Load Switch for Portable Devices
- DC/DC Converter

SOT-523

1. GATE
2. SOURCE
3. DRAIN

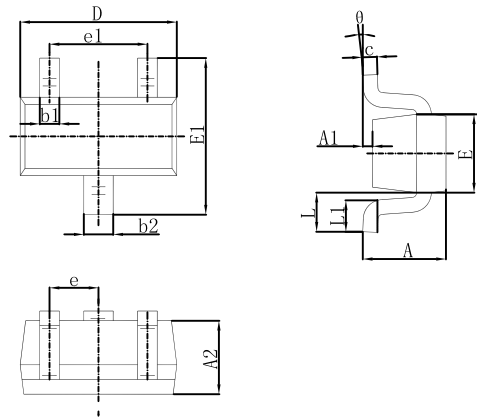


Equivalent Circuit



$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60 V	2.5Ω@10V	300mA
	3Ω@5V	

SOT-523



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Dimensions in inches and (millimeters)

MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source voltage	60	V
V_{GS}	Gate-Source voltage	±20	V
I_D	Drain Current	300	mA
P_D	Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	°C/W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

2N7002T

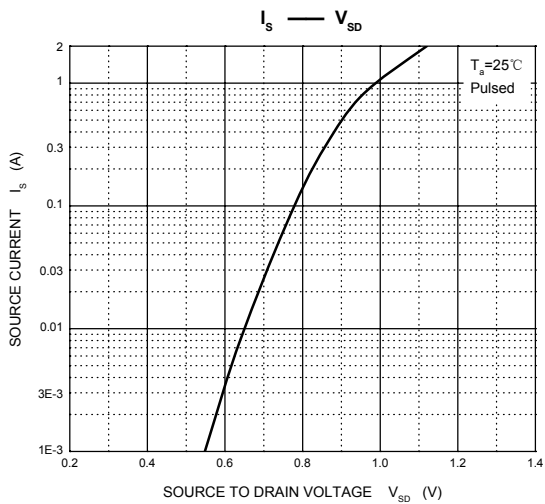
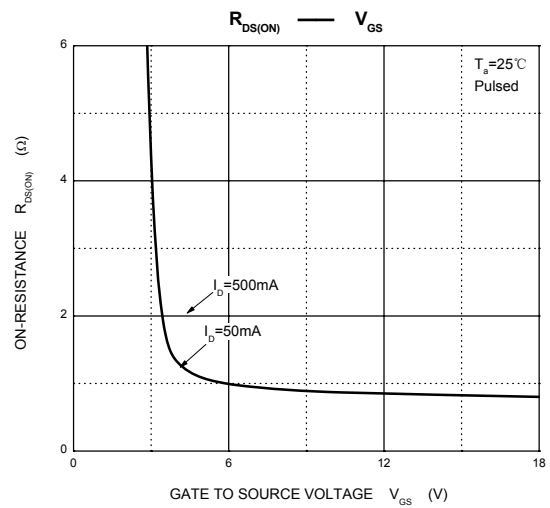
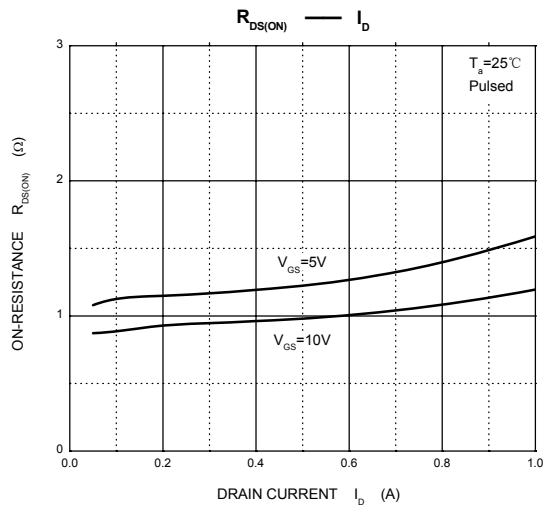
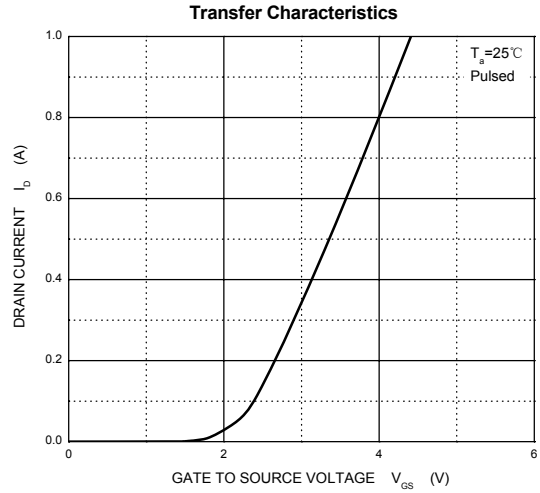
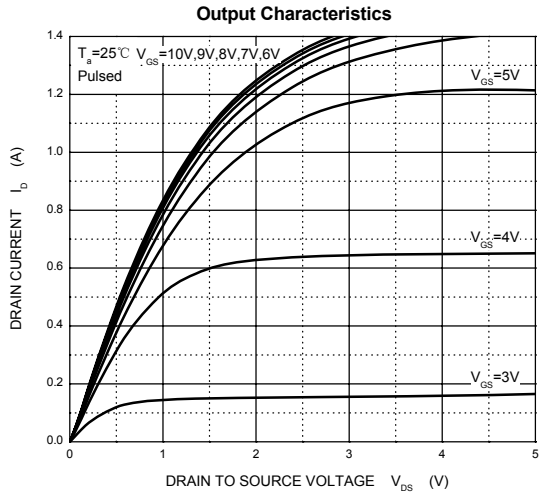
T_a=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0 V, I _D =250 μA	60			V
Gate-Threshold Voltage	V _{th(GS)}	V _{DS} =V _{GS} , I _D =250 μA	1		2.5	
Gate-body Leakage	I _{GSS}	V _{DS} =0 V, V _{GS} =±20 V			±80	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60 V, V _{GS} =0 V			80	nA
On-state Drain Current	I _{D(ON)}	V _{GS} =10 V, V _{DS} =7 V	500			mA
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10 V, I _D =500mA		0.9	2.5	Ω
		V _{GS} =5 V, I _D =50mA		1.1	3	
Forward Trans conductance	g _{fs}	V _{DS} =10 V, I _D =200mA	80			ms
Drain-source on-voltage	V _{DS(on)}	V _{GS} =10V, I _D =500mA			3.75	V
		V _{GS} =5V, I _D =50mA			0.375	V
Diode Forward Voltage	V _{SD}	I _S =115mA, V _{GS} =0 V	0.55		1.2	V
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz			50	pF
Output Capacitance	C _{oss}				25	
Reverse Transfer Capacitance	C _{rss}				5	

SWITCHING TIME

Turn-on Time	t _{d(on)}	V _{DD} =25 V, R _L =50Ω I _D =500mA, V _{GEN} =10 V			20	ns
Turn-off Time	t _{d(off)}		R _G =25 Ω			

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